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# Sumitomo Electric launches 150mm GaN-on-SiC production with AIXTRON Planetary® system

AIX G5+ supports capacity ramp-up for RF device manufacturing

Herzogenrath/Germany, December 03, 2019 – AIXTRON SE (FSE: AIXA), a worldwide leading provider of deposition equipment to the semiconductor industry, announced today that Japanese group Sumitomo Electric Device Innovations, Inc. (SEDI) has ordered an AIX G5+tool with 8x6-inch wafer configuration in order to expand the production capacity of GaN-on-SiC (gallium nitride-on-silicon carbide) radio frequency (RF) devices for wireless applications such as radars, satellite communication and base stations for the rapidly expanding 5G mobile networks. The system is scheduled for delivery in 2019.

SEDI has already been successfully relying on AIXTRON's Showerhead technology for the production of 4-inch GaN epitaxial wafers. The progressive deployment of 5G networks but also the introduction of new technologies like beamforming is foreseen to drive a rapid upturn in demand steering the adoption of more efficient 6-inch substrates for RF applications on AIXTRON's proven Planetary® systems.

By selecting the AIX G5+ Planetary® MOCVD platform, SEDI relies on the tool-of-record for GaN-based high electron mobility transistors (HEMTs) warranting not only superior process yields but also enabling lowest cost of ownership of the market. The system has an unmatched reputation for wafer uniformity and precise process control, which is especially important for device production on cost-intensive silicon carbide wafers. The new reactor is equipped with an EpiCurve TT metrology system as well as with Auto-Feed Forward and P400 UV Pyrometer Close Loop temperature control.

Sumitomo Electric Device Innovations, Inc. has an established industry reputation for providing some of the best RF components available. The company already has a range of GaN HEMT (High Electron Mobility Transistor) devices on offer for radar, mobile phone base-stations, and general applications. These GaN-on-SiC HEMT devices enable high power amplification at operating frequencies of 28-40 GHz and beyond as required by new 5G communication standards.

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#### **About AIXTRON**

AIXTRON SE is a leading provider of deposition equipment to the semiconductor industry. The Company was founded in 1983 and is headquartered in Herzogenrath (near Aachen), Germany, with subsidiaries and sales offices in Asia, United States and in Europe. AIXTRON's technology solutions are used by a diverse range of customers worldwide to build advanced components for electronic and opto-electronic applications based on compound, silicon, or organic semiconductor materials. Such components are used in a broad range of innovative applications, technologies and industries. These include LED applications, display technologies, data storage, data transmission, energy management and conversion, communication, signaling and lighting as well as a range of other leading-edge technologies.

Our registered trademarks: AIXACT®, AIXTRON®, Atomic Level SolutionS®, Close Coupled Showerhead®, CRIUS®, Gas Foil Rotation®, OVPD®, Planetary Reactor®, PVPD®, TriJet®

For further information on AIXTRON (FSE: AIXA, ISIN DE000A0WMPJ6; OTC: AIXNY) please visit our website at: www.aixtron.com.

### About Sumitomo Electric Device Innovations, Inc. (SEDI)

SEDI is a subsidiary company of Sumitomo Electric which produces a wide range of products from optical fibers, cables and components to electronic devices and automotive parts. Through effective research and diversification, Sumitomo Electric has become one of the world's leading companies in information and communication technology. The company operates in about 30 countries, employing more than 270,000 people. Sumitomo Electric reported group net sales of about USD 29 billion for the fiscal year ended March 2019.

For further information, please visit: www.sedi.co.jp

#### **Forward-Looking Statements**

This document may contain forward-looking statements regarding the business, results of operations, financial condition and earnings outlook of AIXTRON. These statements may be identified by words such as "may", "will", "expect", "anticipate", "contemplate", "intend", "plan", "believe", "continue" and "estimate" and variations of such words or similar expressions. These forward-looking statements are based on our current assessments, expectations and assumptions, of which many are beyond control of AIXTRON, and are subject to risks and uncertainties. You should not place undue reliance on these forward-looking statements. Should these risks or uncertainties materialize, or should underlying expectations not occur or assumptions prove incorrect, actual results, performance or achievements of AIXTRON may materially vary from those described explicitly or implicitly in the relevant forward-looking statement. This could result from a variety of factors, such as actual customer orders received by AIXTRON, the level of demand for deposition technology in the market, the timing of final acceptance of products by customers, the condition of financial markets and access to financing for AIXTRON, general conditions in the market for deposition plants and macroeconomic conditions, cancellations, rescheduling or delays in product shipments, production capacity constraints, extended sales and qualification cycles, difficulties in the production process, the general development in the semi-conductor industry, increased competition, fluctuations in exchange rates, availability of public funding, fluctuations and/or changes in interest rates, delays in developing and marketing new products, a deterioration of the general economic situation and any other factors discussed in any reports or other announcements, in particular in the chapter Risks in the Annual Report, filed by AIXTRON. Any forward-looking statements contained in this document are based on current expectations and projections of the executive board based on information available the date hereof. AIXTRON undertakes no obligation to revise or update any forward-looking statements as a result of new information, future events or otherwise, unless expressly required to do so by law.

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